Sheet 1 of 2

FORM PTO-1449 (REV. 7-80) U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 51889/4 US	APPLICATION NO. 10/733,612
INFORMATION DISCLOSURE CITATION	APPLICANT – Douglas R. Hackler, Sr. et al.	
Title: **SRAM Cell**	FILING DATE- December 11, 2003	AU 2818

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Docket Number (Optional)	Application Number
51889/4	10/733,612
Applicant(s) Douglas R. Hackler, Sr. et al.	
Filing Date December 11, 2003	**Group Art Unit** 2818

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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	A2	2002/0180486	12/05/02	Yamashita et al.	326	113	06/25/02
	A3	2002/0084803	07/04/02	Mathew et al.	326	113	12/29/00
	A4	2002/0081808	06/27/02	Forbes	438	283	01/25/02
	A5	2002/0047727	04/25/02	Mizuno	326	113	10/18/01
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	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

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Douglas R. Hackler, Sr. et al.	
FILING: December 11, 2003	GROUP

U.S. PATENT DOCUMENTS

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ATTY. DOCKET NO.	APPLICATION NO.
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		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
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FORM PTO-1449 (REV. 7-80)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 51889/4 US	APPLICATION NO. 10/733,612
INFORMATION DISCLOSURE CITATION		APPLICANT – Douglas R. Hackler, Sr. et al.	
Title: **SRAM Cell**		FILING DATE- December 11, 2003	

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